Impact of pixel size and material budget on resolution(s)

A reminder

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SVT

Inner Barrel (IB)

- 2 curved silicon vertex layers
- 1 curved dual-purpose layer

Outer Barrel (OB)

- 1 stave-based sagitta layer
- 1 stave-based outer layer



Total (active) area ~ 8.5 m²

c.f. https://wiki.bnl.gov/EPIC/index.php?title=Si_Vertex_Tracker

SVT — single track impact resolution

Consider single charged pion tracks at mid-rapidity in fast simulations*,

Recall the default barrel geometry:

Region	Layer	radius [mm]	length [mm]	X/X0
IB	LO	36	270	0.05 %
	L1	48	270	0.05 %
	L2	120	270	0.05 %
OB	L3	270	540	0.25 %
	L4	420	840	0.55 %

The beam-pipe is considered to be at a radius of 31 mm, be made of Beryllium, and have a thickness of 800 μ m so that X/X₀ ~ 0.23%. It is coated internally with a Gold layer of 5 μ m thickness, corresponding to X/X₀ ~ 0.14%.

Consider effects of increased pixel pitch (point resolution) and material in L0-L3 (L4).

The outer (non-MAPS) tracker is not considered in any of the simulations that follow.

* LDT — includes e.g. effect of multiple scattering on angle, though not energy loss

SVT — single track impact resolution

Consider single charged pion tracks at mid-rapidity in fast simulations^{*} and consider effects of increased pixel pitch (point resolution) and material in L0-L3 (L4),



Point resolution and pixel pitch are proportional in these simulations; the usual factor of $\sqrt{12}$.

Pitch is a ~10% and material a ~50% effect at 1 GeV/c in this parameter range.

SVT — single track impact resolution

L0 and L1 are closely spaced in radius and thereby provide a form of redundancy for the track's anchor point near the beam-pipe; it is illustrative to consider the "what if" L0 were inefficient.



Point resolution and pixel pitch are proportional in these simulations; the usual factor of $\sqrt{12}$.

L0 inefficiency is a ~10% effect for $X/X_0 \sim 0.05\%$ and a ~20% effect for $X/X_0 \sim 0.3\%$ at 1 GeV/c.

Consider single charged pion tracks at mid-rapidity in fast simulations^{*} and consider effects of increased pixel pitch (point resolution) and material in L0-L3 (L4),



Point resolution and pixel pitch are proportional in these simulations; the usual factor of $\sqrt{12}$.

Pitch is a ~10% (60%) and material a ~85% (25%) effect at 1 GeV/c (10 GeV/c) in this parameter range.

Consider single charged pion tracks at **backward angles** – here, 174.3° or η ~3 – in the EE disk array in fast simulations, and consider the effects of the shrunk lever arm and pixel pitch,

Recall the (slightly revised) backward geometry:

Region	Disk	z [mm]	inner radius [mm]	outer radius [mm]	X/X0
EE	ED0	-250	36.76	240	0.24 %
	ED1	-450	36.76	415	0.24 %
	ED2	-650	36.76	421.4	0.24 %
	ED3	-850	40	421.4	0.24 %
	ED4	-1050	46.35	421.4	0.24 %

Note that the disks are (now) equidistant; previously ED3 was at -900 mm and ED4 at -1150mm,

The shrunk lever arm serves to accommodate two MPGD disks (in combination with the pfRICH).

Consider single charged pion tracks at **backward angles** – here, 174.3° or η ~-3 – in the EE disk array in fast simulations, and consider the effects of the shrunk lever arm and pixel pitch,



Note, disk ED0 is outside of the acceptance at this angle so that L ~ 60 cm with ED4 at -105 cm, Effect of lever arm is ~19% for 1 - 10 GeV/c and less than the ratio of L² ~ 35%, Effect of pixel pitch is ~25% at 10 GeV/c for a change in pitch from 10 to 22 µm.

The disks are estimated to each have $X/X_0 \sim 0.24\%$; it is illustrative to consider "what if" this were to increase.



A ~25% effect from a ~50% increase in X/X₀ at 1 GeV/c (indeed; expect $\sqrt{-\text{scaling all else being equal}}$, (Aside, the "floor" in dp/p also scales as B⁻¹)

Closing comments

Considered mid-rapidity and backward charged pion tracks:

- 10% effect on mid-rapidity impact parameter from pixel pitch (10 to 22 μm) at 1 GeV/c,
- 50% effect on mid-rapidity impact parameter if material increases (X/X₀ ~ 0.05% to ~0.30%) at 1 GeV/c,
- ~25 μm default mid-rapidity impact parameter at 1 GeV/c, decreasing to less than 10 μm at 10 GeV/c,
- (ct ~123 μm for D0, ~60 μm for $\Lambda_c),$
- 10% effect on mid-rapidity dp/p from pixel pitch (10 to 22 μ m) at 1 GeV/c,
- 85% effect on mid-rapidity dp/p if material increases (X/X $_0$ ~ 0.05% to ~0.30%) at 1 GeV/c,
- ~0.35% default dp/p at mid-rapidity at 1 GeV/c,
- Relative impact changes (reverses) with increasing p; 60% from pitch and 25% from material at 10 GeV/c,
- Anticipate backward dp/p to worsen by ~19% from reduced lever arm (does not scale as L²; slower),
- dp/p essentially unaffected by an increase of pixel pitch from 10 to 22 μm* up to p ~ 3 GeV/c; 25% effect at 10 GeV/c,
- 25% effect on dp/p from 50% increase in X/X₀ (as expected from $\sqrt{-scaling}$),
- dp/p ~ 4% for 1 \eta ~ -3
- Will prepare a short writeup, time-permitting.